SYNCHRONOUS SRAM

64K x 18 SRAM

+3.3V SUPPLY, FULLY REGISTERED INPUTS AND OUTPUTS AND BURST COUNTER

FEATURES

- Fast access times: 4.5, 5, 6, 7 and 8ns
- Fast $\overline{OE}$: 5 and 6ns
- Single +3.3V ±5% power supply
- 5V-tolerant I/O
- Common data inputs and data outputs
- Individual BYTE WRITE control and GLOBAL WRITE
- Three chip enables for simple depth expansion and address pipelining
- Clock controlled, registered, address, data I/O and control for fully pipelined applications
- Internally self-timed WRITE cycle
- WRITE pass-through capability
- Burst control pins (interleaved or linear burst)
- Automatic power-down for portable applications
- High density, high speed packages
- Low capacitive bus loading
- High 30pF output drive capability at rated access time
- DIMMs also available

OPTIONS — MARKING

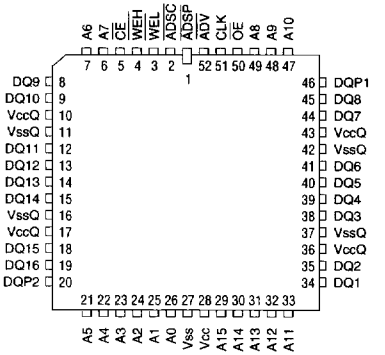
- Timing
  - 4.5ns access/8ns cycle — -4.5
  - 5ns access/10ns cycle — -5
  - 6ns access/12ns cycle — -6
  - 7ns access/15ns cycle — -7
  - 8ns access/20ns cycle — -8
- Packages
  - 52-pin PLCC — EJ
  - 100-pin TQFP — LG
- Low power — P
- 2V data retention, low power — L
- Part Number Example: MT58LC64K18C4LG-7 P

Part Number Examples

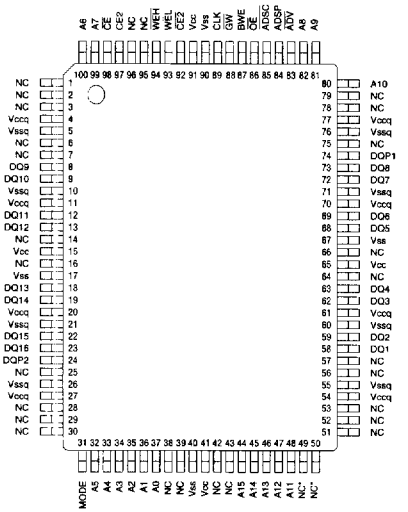
BASE PART NO.	VERSION SUFFIX	PACKAGE	BURST SEQUENCE
MT58LC64K18	A6	EJ	Linear
MT58LC64K18	C4	EJ	Interleaved
MT58LC64K18	C4	LG	Interleaved (Mode = NC) Linear (Mode = GND)

PIN ASSIGNMENT (Top View)

52-Pin PLCC
(SB-1)



100-Pin TQFP
(SC-1)



*Pin 49 is reserved for A16, pin 50 for A17

SYNCHRONOUS SRAM

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GENERAL DESCRIPTION

The Micron SyncBurst™ SRAM family employs high-speed, low-power CMOS designs using a four-transistor memory cell. Micron SRAMs are fabricated using double-layer metal, double-layer polysilicon technology.

The MT58LC64K18 SRAM integrates a 64K x 18 SRAM core with advanced synchronous peripheral circuitry and a 2-bit burst counter. All synchronous inputs pass through registers controlled by a positive-edge-triggered single clock input (CLK). The synchronous inputs include all addresses, all data inputs, active LOW chip enable ($\overline{CE}$), two additional chip enables for easy depth expansion (CE2, $\overline{CE2}$), burst control inputs ($\overline{ADSC}$, $\overline{ADSP}$, $\overline{ADV}$) byte write enables ($\overline{WEH}$, $\overline{WEL}$, $\overline{BWE}$) and global write ($\overline{GW}$).

Asynchronous inputs include the output enable ($\overline{OE}$), clock (CLK) and burst mode (MODE). The data-out (Q), enabled by $\overline{OE}$, is also asynchronous. WRITE cycles can be from one to two bytes wide as controlled by the write control inputs.

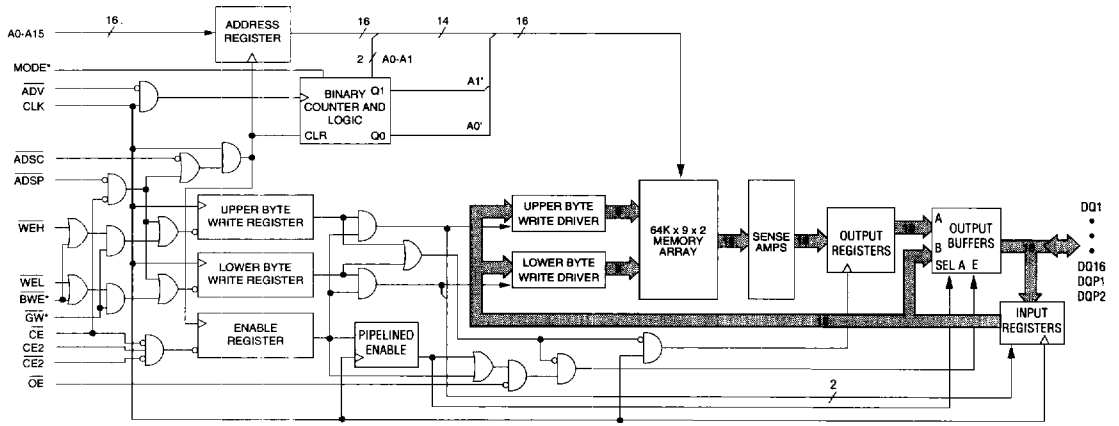
Burst operation can be initiated with either address status processor ($\overline{ADSP}$) or address status controller ($\overline{ADSC}$) input pins. Subsequent burst addresses can be internally generated as controlled by the burst advance pin ($\overline{ADV}$).

Address and write control are registered on-chip to simplify WRITE cycles. This allows self-timed WRITE cycles. Individual byte enables allow individual bytes to be written. $\overline{WEL}$ controls DQ1-DQ8 and DQP1. $\overline{WEH}$ controls DQ9-DQ16 and DQP2, conditioned by $\overline{BWE}$ being LOW. $\overline{GW}$ LOW causes all bytes to be written. WRITE pass-through makes written data immediately available at the output register during the READ cycle following a WRITE as controlled solely by $\overline{OE}$ to improve cache system response. The device incorporates an additional pipelined enable register to allow depth expansion without penalizing system performance.

The "L" version of this device has a data retention option which is useful for battery backup mode of operation. Although the part is not guaranteed to operate functionally below Vcc MIN (3.1V), it will retain data with a minimum of power dissipation.

The MT58LC64K18 operates from a +3.3V power supply and all inputs and outputs are TTL-compatible and 5V-tolerant. The device is ideally suited for Pentium™ and PowerPC™ pipelined systems and systems that benefit from a very wide high-speed data bus.

FUNCTIONAL BLOCK DIAGRAM



*LG package only

NOTE: 1. The Functional Block Diagram illustrates simplified device operation. See Truth Table, pin descriptions and timing diagrams for detailed information.

BURST ADDRESS TABLE (MODE = NC or MT58LC64K18C4 EJ device)

First Address (external)	Second Address (internal)	Third Address (internal)	Fourth Address (internal)
X...X00	X...X01	X...X10	X...X11
X...X01	X...X00	X...X11	X...X10
X...X10	X...X11	X...X00	X...X01
X...X11	X...X10	X...X01	X...X00

BURST ADDRESS TABLE (MODE = GND or MT58LC64K18A4 EJ device)

First Address (external)	Second Address (internal)	Third Address (internal)	Fourth Address (internal)
X...X00	X...X01	X...X10	X...X11
X...X01	X...X10	X...X11	X...X00
X...X10	X...X11	X...X00	X...X01
X...X11	X...X00	X...X01	X...X10

PIN DESCRIPTIONS

PLCC PINS	TQFP PINS	SYMBOL	TYPE	DESCRIPTION
26, 25, 24, 23, 22, 21, 7, 6, 49, 48, 47, 33, 32, 31, 30, 29	37, 36, 35, 34, 33, 32, 100, 99, 82, 81, 80, 48, 47, 46, 45, 44	A0-A15	Input	Synchronous Address Inputs: These inputs are registered and must meet the setup and hold times around the rising edge of CLK.
4, 3	94, 93	$\overline{WEH}$, $\overline{WEL}$	Input	Synchronous Byte Write Enables: These active LOW inputs allow individual bytes to be written and must meet the setup and hold times around the rising edge of CLK. A byte write enable is LOW for a WRITE cycle and HIGH for a READ cycle. $\overline{WEL}$ controls DQ1-DQ8 and DQP1. $\overline{WEH}$ controls DQ9-DQ16 and DQP2. Data I/O are tristated if either of these inputs are LOW.
n/a	87	$\overline{BWE}$	Input	Byte Write Enable: This active LOW input permits byte write operations and must meet the setup and hold times around the rising edge of CLK.
n/a	88	$\overline{GW}$	Input	Global Write: This active LOW input allows a full 18-bit WRITE to occur independent of the $\overline{BWE}$ and $\overline{WEn}$ lines and must meet the setup and hold times around the rising edge of CLK.
51	89	CLK	Input	Clock: This signal registers the address, data, chip enable, byte write enables and burst control inputs on its rising edge. All synchronous inputs must meet setup and hold times around the clock's rising edge.
5	98	$\overline{CE}$	Input	Synchronous Chip Enable: This active LOW input is used to enable the device and conditions internal use of $\overline{ADSP}$. This input is sampled only when a new external address is loaded.
n/a	92	$\overline{CE2}$	Input	Synchronous Chip Enable: This active LOW input is used to enable the device. This input is sampled only when a new external address is loaded.

PIN DESCRIPTIONS (continued)

PLCC PINS	TQFP PINS	SYMBOL	TYPE	DESCRIPTION
n/a	97	CE2	Input	Synchronous Chip Enable: This active HIGH input is used to enable the device. This input is sampled only when a new external address is loaded.
50	86	$\overline{OE}$	Input	Output Enable: This active LOW asynchronous input enables the data I/O output drivers.
52	83	$\overline{ADV}$	Input	Synchronous Address Advance: This active LOW input is used to advance the internal burst counter, controlling burst access after the external address is loaded. A HIGH on this pin effectively causes wait states to be generated (no address advance). This pin must be HIGH at the rising edge of the first clock after an $\overline{ADSP}$ cycle is initiated if a WRITE cycle is desired (to ensure use of correct address).
1	84	$\overline{ADSP}$	Input	Synchronous Address Status Processor: This active LOW input interrupts any ongoing burst, causing a new external address to be registered. A READ is performed using the new address, independent of the byte write enables and $\overline{ADSC}$ but dependent upon $\overline{CE}$ being LOW.
2	85	$\overline{ADSC}$	Input	Synchronous Address Status Controller: This active LOW input interrupts any ongoing burst, causing a new external address to be registered. A READ or WRITE is performed using the new address if $\overline{CE}$ is LOW. $\overline{ADSC}$ is also used to place the chip into power-down state when $\overline{CE}$ is HIGH.
n/a	31	MODE	Input	Mode: This input selects the burst sequence. A LOW on this pin selects LINEAR BURST. A NC or HIGH on this pin selects INTERLEAVED BURST. Do not alter input state while device is operating.
34, 35, 38, 39, 40, 41, 44, 45, 8, 9, 12, 13, 14, 15, 18, 19	58, 59, 62, 63, 68, 69, 72, 73, 8, 9, 12, 13, 18, 19, 22, 23	DQ1-DQ16	Input/ Output	SRAM Data I/O: Low Byte is DQ1-DQ8. High Byte is DQ9-DQ16. Input data must meet setup and hold times around the rising edge of CLK.
46, 20	74, 24	DQP1, DQP2	Input/ Output	Parity Data I/O: Low Byte Parity is DQP1. High Byte Parity is DQP2.
28	15, 41, 65, 91	V_{CC}	Supply	Power Supply: +3.3V ±5%
27	17, 40, 67, 90	V_{SS}	Supply	Ground: GND
10, 17, 36, 43	4, 11, 20, 28, 54, 61, 70, 77	V_{CCQ}	Supply	Isolated Output Buffer Supply: +3.3V ±5%
11, 16, 37, 42	6, 10, 21, 26, 55, 60, 71, 76	V_{SSQ}	Supply	Isolated Output Buffer Ground: GND
	1, 2, 3, 6, 7, 14, 16, 25, 28, 29, 30, 38, 39, 42, 43, 49, 50, 51, 52, 53, 56, 57, 64, 66, 75, 78, 79, 95, 96	NC	-	No Connect: These signals are not internally connected. These signals may be connected to ground to improve package heat dissipation.

PARTIAL TRUTH TABLE FOR WRITEs

Function	$\overline{GW}$	$\overline{BWE}$	$\overline{WEL}$	$\overline{WEH}$
READ	H	H	X	X
READ	H	L	H	H
WRITE Low Byte	H	L	L	H
WRITE High Byte	H	L	H	L
WRITE all bytes	H	L	L	L
WRITE all bytes	L	X	X	X

PASS-THROUGH TRUTH TABLE

PREVIOUS CYCLE		PRESENT CYCLE				NEXT CYCLE
OPERATION	$\overline{WEs}$	OPERATION	$\overline{CE}$	$\overline{WEs}$	$\overline{OE}$	OPERATION
Initiate WRITE cycle, all bytes Address = A(n-1), data = D(n-1)	All L[2,3]	Initiate READ cycle Register A(n), Q = D(n-1)	L	H	L	Read D(n)
Initiate WRITE cycle, all bytes Address = A(n-1), data = D(n-1)	All L[2,3]	No new cycle Q = D(n-1)	H	H	L	No carry-over from previous cycle
Initiate WRITE cycle, all bytes Address = A(n-1), data = D(n-1)	All L[2,3]	No new cycle Q = HIGH-Z	H	H	H	No carry-over from previous cycle
Initiate WRITE cycle, one byte Address = A(n-1), data = D(n-1)	One L[2]	No new cycle Q = D(n-1) for one byte	H	H	L	No carry-over from previous cycle

NOTE: 1. Previous cycle may be either BURST or NONBURST cycle.
2. $\overline{BWE}$ is LOW when one or two $\overline{WEn}$ is LOW.
3. $\overline{GW}$ LOW will yield identical results.

TRUTH TABLE

OPERATION	ADDRESS USED	$\overline{CE}$	$\overline{CE2}$	CE2	$\overline{ADSP}$	$\overline{ADSC}$	$\overline{ADV}$	WRITE	$\overline{OE}$	CLK	DQ
Deselected Cycle, Power-down	None	H	X	X	X	L	X	X	X	L-H	High-Z
Deselected Cycle, Power-down	None	L	X	L	L	X	X	X	X	L-H	High-Z
Deselected Cycle, Power-down	None	L	H	X	L	X	X	X	X	L-H	High-Z
Deselected Cycle, Power-down	None	L	X	L	H	L	X	X	X	L-H	High-Z
Deselected Cycle, Power-down	None	L	H	X	H	L	X	X	X	L-H	High-Z
READ Cycle, Begin Burst	External	L	L	H	L	X	X	X	L	L-H	Q
READ Cycle, Begin Burst	External	L	L	H	L	X	X	X	H	L-H	High-Z
WRITE Cycle, Begin Burst	External	L	L	H	H	L	X	L	X	L-H	D
READ Cycle, Begin Burst	External	L	L	H	H	L	X	H	L	L-H	Q
READ Cycle, Begin Burst	External	L	L	H	H	L	X	H	H	L-H	High-Z
READ Cycle, Continue Burst	Next	X	X	X	H	H	L	H	L	L-H	Q
READ Cycle, Continue Burst	Next	X	X	X	H	H	L	H	H	L-H	High-Z
READ Cycle, Continue Burst	Next	H	X	X	X	H	L	H	L	L-H	Q
READ Cycle, Continue Burst	Next	H	X	X	X	H	L	H	H	L-H	High-Z
WRITE Cycle, Continue Burst	Next	X	X	X	H	H	L	L	X	L-H	D
WRITE Cycle, Continue Burst	Next	H	X	X	X	H	L	L	X	L-H	D
READ Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	L	L-H	Q
READ Cycle, Suspend Burst	Current	X	X	X	H	H	H	H	H	L-H	High-Z
READ Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	L	L-H	Q
READ Cycle, Suspend Burst	Current	H	X	X	X	H	H	H	H	L-H	High-Z
WRITE Cycle, Suspend Burst	Current	X	X	X	H	H	H	L	X	L-H	D
WRITE Cycle, Suspend Burst	Current	H	X	X	X	H	H	L	X	L-H	D

NOTE:
1. X means "don't care." H means logic HIGH. L means logic LOW. $\overline{WRITE}$=L means any one or more byte write enable signals ($\overline{WEL}$ or $\overline{WEH}$) and $\overline{BWE}$ are LOW or $\overline{GW}$ is LOW. $\overline{WRITE}$=H means all byte write enable signals are HIGH.
2. $\overline{WEL}$ enables WRITEs to DQ1-DQ8, DQP1. $\overline{WEH}$ enables WRITEs to DQ9-DQ16, DQP2.
3. All inputs except $\overline{OE}$ must meet setup and hold times around the rising edge (LOW to HIGH) of CLK.
4. Wait states are inserted by suspending burst.
5. For a WRITE operation following a READ operation, $\overline{OE}$ must be HIGH before the input data required setup time and held HIGH throughout the input data hold time.
6. This device contains circuitry that will ensure the outputs will be in High-Z during power-up.
7. $\overline{ADSP}$ LOW always initiates an internal READ at the L-H edge of CLK. A WRITE is performed by setting one or more byte write enable signals and $\overline{BWE}$ LOW or $\overline{GW}$ LOW for the subsequent L-H edge of CLK. Refer to WRITE timing diagram for clarification.

ABSOLUTE MAXIMUM RATINGS*

Voltage on V_{CC} Supply Relative to Vss ..... -0.5V to +4.6V
V_{IN} ..... -0.5V to +6V
Storage Temperature (plastic) ..... -55°C to +150°C
Junction Temperature** ..... +150°C
Short Circuit Output Current 100mA

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

**Maximum junction temperature depends upon package type, cycle time, loading, ambient temperature and airflow. See technical note TN-05-14 for more information.

ELECTRICAL CHARACTERISTICS AND RECOMMENDED DC OPERATING CONDITIONS

(0°C ≤ T_A ≤ 70°C; V_{CC} = 3.3V ±5% unless otherwise noted)

DESCRIPTION	CONDITIONS	SYMBOL	MIN	MAX	UNITS	NOTES
Input High (Logic 1) Voltage		V_{IH}	2.0	5.5	V	1, 2
Input Low (Logic 0) Voltage		V_{IL}	-0.3	0.8	V	1, 2
Input Leakage Current	0V ≤ V_{IN} ≤ V_{CC}	I_{LI}	-1	1	µA	14
Output Leakage Current	Output(s) disabled, 0V ≤ V_{OUT} ≤ V_{CC}	I_{LO}	-1	1	µA	
Output High Voltage	I_{OH} = -4.0mA	V_{OH}	2.4		V	1, 11
Output Low Voltage	I_{OL} = 8.0mA	V_{OL}		0.4	V	1, 11
Supply Voltage		V_{CC}	3.1	3.5	V	1

					MAX						
DESCRIPTION	CONDITIONS	SYM	VER	TYP	-4.5	-5	-6	-7	-8	UNITS	NOTES
Power Supply Current: Operating	Device selected; all inputs ≤ V_{IL} or ≥ V_{IH}; cycle time ≥ ^tKC MIN; Vcc = MAX; outputs open	I_{CC}	ALL	180	400	335	300	250	210	mA	3, 12, 13
Power Supply Current: Idle	Device selected; V_{CC} = MAX; $\overline{ADSC}$, $\overline{ADSP}$, $\overline{GW}$, $\overline{BWs}$, $\overline{ADV}$ ≥ V_{IH}; all inputs ≤ Vss +0.2 or ≥ Vcc -0.2; cycle time ≥ ^tKC MIN	I_{CC1}	ALL	30	65	60	55	50	45	mA	12, 13
CMOS Standby	Device deselected; Vcc = MAX; all inputs ≤ Vss +0.2 or ≥ Vcc -0.2; all inputs static; CLK frequency = 0	I_{SB2}	STD	0.5	5	5	5	5	5	mA	12, 13
			P	0.2	2	2	2	2	2	mA	
TTL Standby	Device deselected; Vcc = MAX; all inputs ≤ V_{IL} or ≥ V_{IH}; all inputs static; CLK frequency = 0	I_{SB3}	STD	15	25	25	25	25	25	mA	12, 13
			P	8	18	18	18	18	18	mA	
Clock Running	Device deselected; Vcc = MAX; all inputs ≤ Vss +0.2 or ≥ Vcc -0.2; CLK cycle time ≥ ^tKC MIN	I_{SB4}	ALL	30	65	60	55	50	45	mA	12, 13

CAPACITANCE

DESCRIPTION	CONDITIONS	SYMBOL	TYP	MAX	UNITS	NOTES
Input Capacitance	T_A = 25°C; f = 1 MHz	C_I	3	4	pF	4
Input/Output Capacitance (DQ)	Vcc = 3.3V	C_O	6	7	pF	4

THERMAL CONSIDERATIONS

DESCRIPTION	CONDITIONS	SYMBOL	PLCC TYP	TQFP TYP	UNITS	NOTES
Thermal resistance - Junction to Ambient	Still air, soldered on 4.25 x	θ_{JA}	45	20	°C/W	
Thermal resistance - Junction to Case	1.125 inch 4-layer PCB	θ_{JC}	15	1	°C/W	

ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS

(Note 5) (0°C ≤ T_A ≤ 70°C; Vcc = 3.3V ±5%)

DESCRIPTION		-4.5		-5		-6		-7		-8			
	SYM	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNITS	NOTES
Clock													
Clock cycle time	^tKC	8		10		12		15		20		ns	
Clock HIGH time	^tKH	3		4		4.5		5		6		ns	
Clock LOW time	^tKL	3		4		4.5		5		6		ns	
Output Times													
Clock to output valid	^tKQ		4.5		5		6		7		8	ns	
Clock to output invalid	^tKQX	2		2		2		2		2		ns	
Clock to output in Low-Z	^tKQLZ	4		4		5		5		5		ns	6, 7
Clock to output in High-Z	^tKQHZ		4.5		5		5		6		6	ns	6, 7
$\overline{OE}$ to output valid	^tOEQ		4.5		5		5		5		6	ns	9
$\overline{OE}$ to output in Low-Z	^tOELZ	0		0		0		0		0		ns	6, 7
$\overline{OE}$ to output in High-Z	^tOEHZ		3		4		5		6		6	ns	6, 7
Setup Times													
Address	^tAS	2.5		2.5		2.5		2.5		3		ns	8, 10
Address Status ($\overline{ADSC}$, $\overline{ADSP}$)	^tADSS	2.5		2.5		2.5		2.5		3		ns	8, 10
Address Advance ($\overline{ADV}$)	^tAAS	2.5		2.5		2.5		2.5		3		ns	8, 10
Write Signals ($\overline{WEL}$, $\overline{WEH}$, $\overline{BWE}$, $\overline{GW}$)	^tWS	2.5		2.5		2.5		2.5		3		ns	8, 10
Data-in	^tDS	2.5		2.5		2.5		2.5		3		ns	8, 10
Chip Enables ($\overline{CE}$, $\overline{CE2}$, CE2)	^tCES	2.5		2.5		2.5		2.5		3		ns	8, 10
Hold Times													
Address	^tAH	0.5		0.5		0.5		0.5		0.5		ns	8, 10
Address Status ($\overline{ADSC}$, $\overline{ADSP}$)	^tADSH	0.5		0.5		0.5		0.5		0.5		ns	8, 10
Address Advance ($\overline{ADV}$)	^tAAH	0.5		0.5		0.5		0.5		0.5		ns	8, 10
Write Signals ($\overline{WEL}$, $\overline{WEH}$, $\overline{BWE}$, $\overline{GW}$)	^tWH	0.5		0.5		0.5		0.5		0.5		ns	8, 10
Data-in	^tDH	0.5		0.5		0.5		0.5		0.5		ns	8, 10
Chip Enables ($\overline{CE}$, $\overline{CE2}$, CE2)	^tCEH	0.5		0.5		0.5		0.5		0.5		ns	8, 10

AC TEST CONDITIONS

Input pulse levels	Vss to 3.0V
Input rise and fall times	1.5ns
Input timing reference levels	1.5V
Output reference levels	1.5V
Output load	See Figures 1 and 2

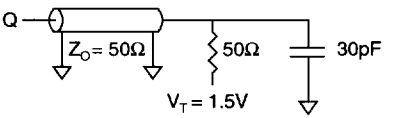


Fig. 1 OUTPUT LOAD EQUIVALENT

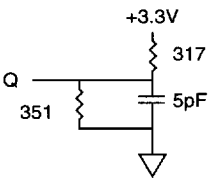


Fig. 2 OUTPUT LOAD EQUIVALENT

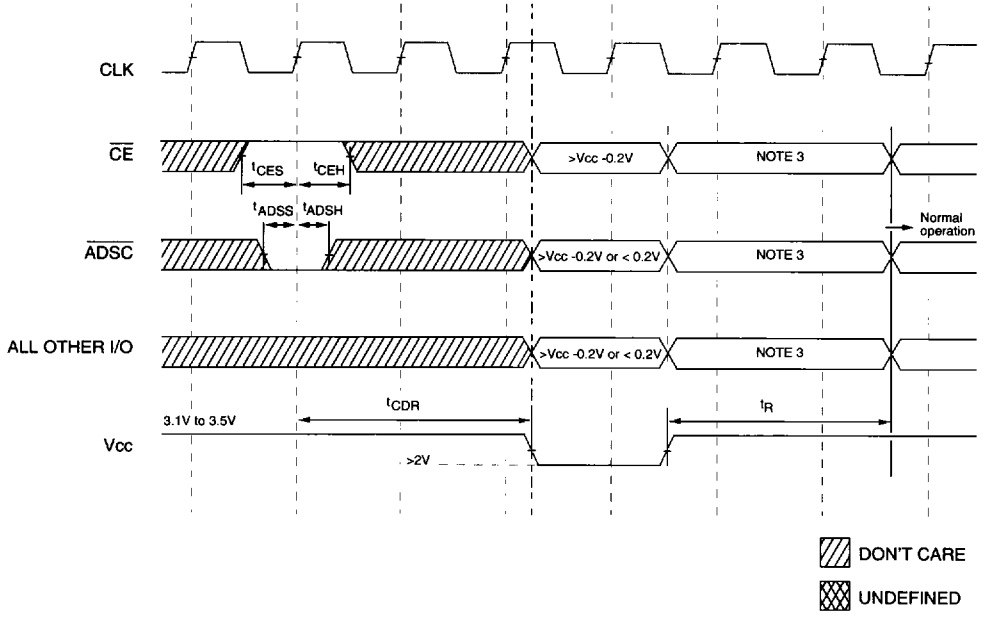
NOTES

1. All voltages referenced to Vss (GND).
2. Overshoot: $V_{IH} \leq +6.0V$ for $t \leq {}^tKC/2$.
   Undershoot: $V_{IL} \geq -2.0V$ for $t \leq {}^tKC/2$.
   Power-up: $V_{IH} \leq +6.0V$ and $Vcc \leq 3.1V$ for $t \leq 200ms$
3. Icc is given with no output current. Icc increases with greater output loading and faster cycle times.
4. This parameter is sampled.
5. Test conditions as specified with the output loading as shown in Fig. 1 unless otherwise noted.
6. Output loading is specified with C_L = 5pF as in Fig. 2. Transition is measured ±500mV from steady state voltage.
7. At any given temperature and voltage condition, ${}^tKQHZ$ is less than ${}^tKQLZ$ and ${}^tOEHZ$ is less than ${}^tOELZ$.
8. A WRITE cycle is defined by at least one byte write enable LOW and $\overline{ADSP}$ HIGH for the required setup and hold times. A READ cycle is defined by all byte write enables HIGH and ($\overline{ADSC}$ or $\overline{ADV}$ LOW) or $\overline{ADSP}$ LOW for the required setup and hold times.
9. $\overline{OE}$ is a "don't care" when a byte write enable is sampled LOW.
10. This is a synchronous device. All addresses must meet the specified setup and hold times for all rising edges of CLK when either $\overline{ADSP}$ or $\overline{ADSC}$ is LOW and chip enabled. All other synchronous inputs must meet the setup and hold times with stable logic levels for all rising edges of clock (CLK) when the chip is enabled. Chip enable must be valid at each rising edge of CLK (when either $\overline{ADSP}$ or $\overline{ADSC}$ is LOW) to remain enabled.
11. The load used for V_{OH}, V_{OL} testing is shown in Fig. 2. AC load current is higher than the shown DC values. AC I/O curves are available upon request.
12. "Device Deselected" means device is in POWER-DOWN mode as defined in the Truth Table. "Device Selected" means device is active (not in POWER-DOWN mode).
13. Typical values are measured at 3.3V, 25°C and 20ns cycle time.
14. MODE pin has an internal pull-up and exhibits an input leakage current of ±10µA.
15. Typical values are measured at 25°C.
16. The device must have a deselect cycle applied at least two clock cycles before data retention mode is entered.

DATA RETENTION ELECTRICAL CHARACTERISTICS (L version only)

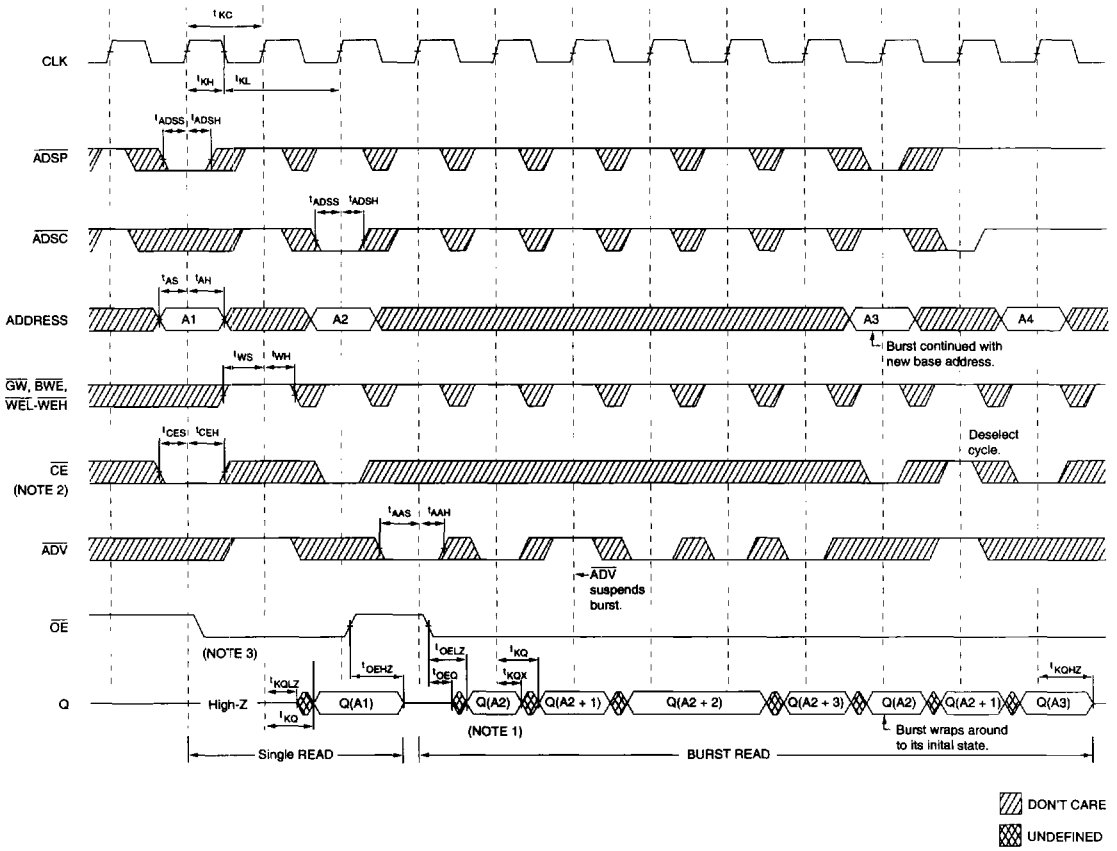
DESCRIPTION	CONDITIONS	SYMBOL	MIN	MAX	UNITS	NOTES
Vcc for Retention Data		V_{DR}	2			V
Data Retention Current	$\overline{CE}$, $\overline{CE2}$ ≥ (Vcc -0.2V), CE2 ≤ 0.2V VIN ≥ (Vcc -0.2V) or ≤ 0.2V Vcc = 2V	I_{CCDR}		TBD	µA	15
Chip Deselect to Data Retention Time		^tCDR	2 ^tKC		ns	4, 16
Operation Recovery Time		^tR	2 ^tKC		ns	4

LOW Vcc DATA RETENTION WAVEFORM



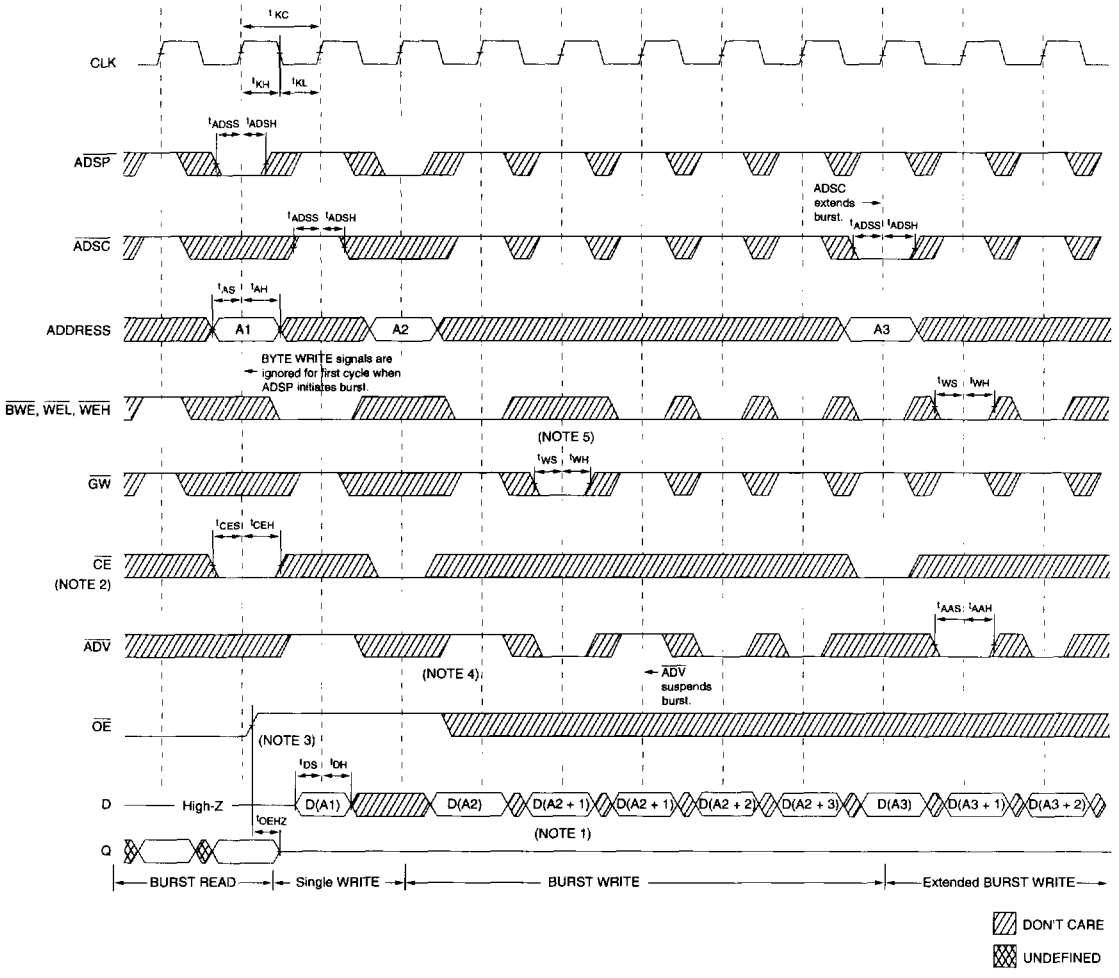
NOTE:
1. All inputs must be ≥ Vcc - 0.2V or ≤ 0.2V to guarantee I_{CCDR} in data retention mode. If inputs are between these levels or left floating, I_{CCDR} may be exceeded.
2. Only one of the available deselect cycle sequences is shown above ($\overline{CE}$ = HIGH, $\overline{ADSC}$ = LOW). Any of the other deselect cycle sequences may also be used.
3. The device control signals should be in a deselect state between the rising edge of Vcc and until ^tR is met.

READ TIMING



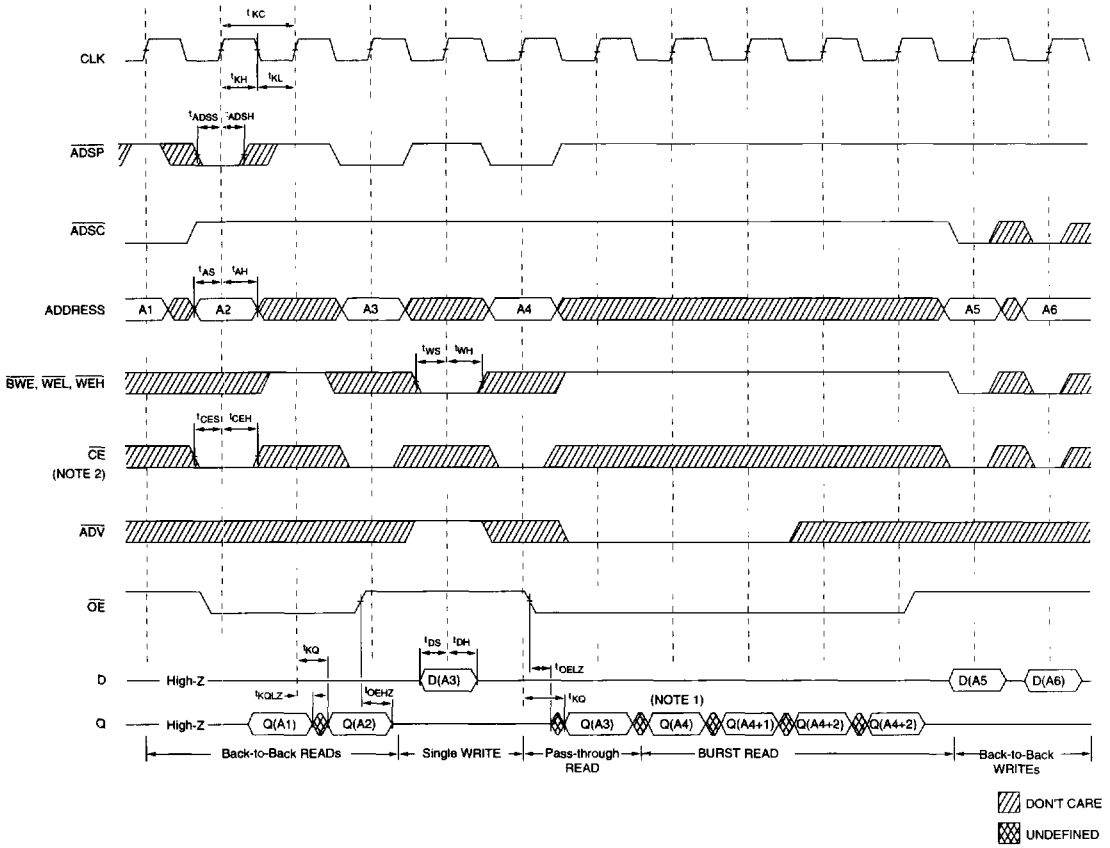
NOTE:
1. Q(A2) refers to output from address A2. Q(A2+1) refers to output from the next internal burst address following A2.
2. $\overline{CE2}$ and CE2 have timing identical to $\overline{CE}$. On this diagram, when $\overline{CE}$ is LOW, $\overline{CE2}$ is LOW and CE2 is HIGH. When $\overline{CE}$ is HIGH, $\overline{CE2}$ is HIGH and CE2 is LOW.
3. Timing is shown assuming that the device was not enabled before entering into this sequence. $\overline{OE}$ does not cause Q to be driven until after the following clock rising edge.

WRITE TIMING



NOTE:
1. Q(A2) refers to output from address A2. Q(A2+1) refers to output from the next internal burst address following A2.
2. $\overline{CE2}$ and CE2 have timing identical to $\overline{CE}$. On this diagram, when $\overline{CE}$ is LOW, $\overline{CE2}$ is LOW and CE2 is HIGH. When $\overline{CE}$ is HIGH, $\overline{CE2}$ is HIGH and CE2 is LOW.
3. $\overline{OE}$ must be HIGH before the input data setup and held HIGH throughout the data hold time. This prevents input/output data contention for the time period prior to the byte write enable inputs being sampled.
4. $\overline{ADV}$ must be HIGH to permit a WRITE to the loaded address.
5. Full width WRITE can be initiated by $\overline{GW}$ LOW or $\overline{GW}$ HIGH and $\overline{BWE}$, $\overline{WEL}$ and $\overline{WEH}$ LOW.

READ/WRITE TIMING



NOTE:
1. Q(A4) refers to output from address A4. Q(A4+1) refers to output from the next internal burst address following A4.
2. $\overline{CE2}$ and CE2 have timing identical to $\overline{CE}$. On this diagram, when $\overline{CE}$ is LOW, $\overline{CE2}$ is LOW and CE2 is HIGH. When $\overline{CE}$ is HIGH, $\overline{CE2}$ is HIGH and CE2 is LOW.
3. The data bus (Q) remains in High-Z following a WRITE cycle unless an $\overline{ADSP}$, $\overline{ADSC}$ or $\overline{ADV}$ cycle is performed.
4. $\overline{GW}$ is HIGH.
5. Back-to-back READs may be controlled by either $\overline{ADSP}$ or $\overline{ADSC}$.

APPLICATION INFORMATION

LOAD DERATING CURVES

The Micron 64K x 18 Synchronous SRAM timing is dependent upon the capacitive loading on the outputs. The data sheet is written assuming a load of 30pF. Access time changes with load capacitance as follows:

$\Delta^tKQ = 0.016$ ns/pF x ΔC_L pF.
(Note: this is preliminary information subject to change.)

For example, if the SRAM loading is 22pF, ΔC_L is -8pF (8pF less than rated load). The clock to valid output time of the SRAM is reduced by 0.016 x 8 = 0.128ns. If the device is an 8ns part, the worst case ^tKQ becomes 7.87ns (approximately).

Consult the factory for copies of I/O current versus voltage curves and capacitive loading derating curves.

DEPTH EXPANSION

The Micron 64K x 18 Synchronous SRAM incorporates two additional chip enables to facilitate simple depth expansion. As shown in Figure 3, this permits easy cache upgrades from 64K depth to 128K depth with no extra logic. The chip enables are pipelined to allow contention-free transition between Micron devices which are physically and electrically close together.

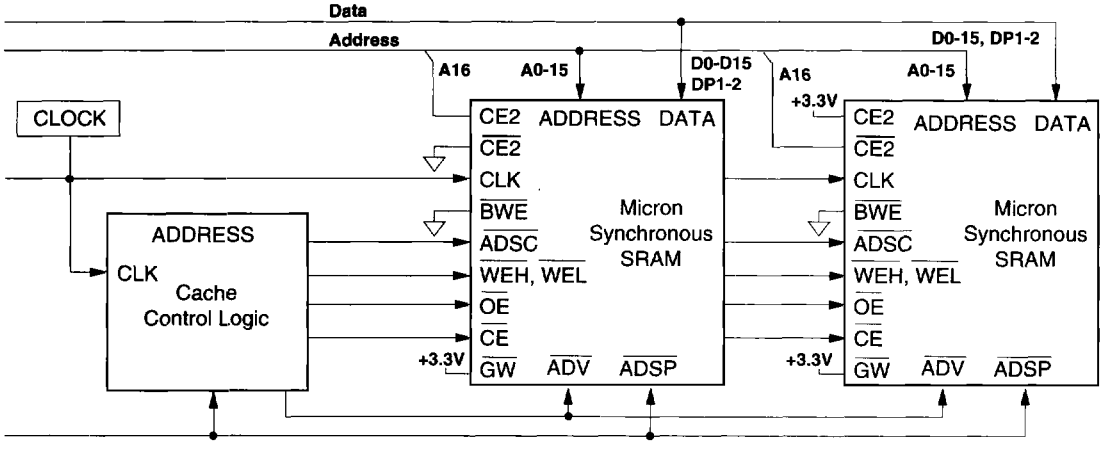


Figure 3
DEPTH EXPANSION FROM 64K x 18 TO 128K x 18 USING TQFP PACKAGES

APPLICATION EXAMPLES

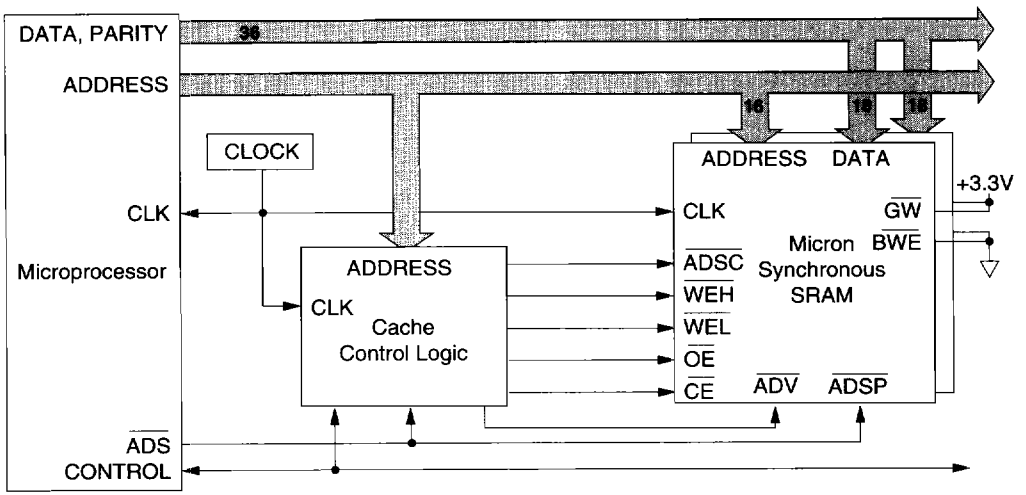


Figure 4
256K BYTE 50 MHz SECONDARY CACHE WITH PARITY AND BURST USING TWO MT58LC64K18C4LG-8 SYNCBURST SRAMs

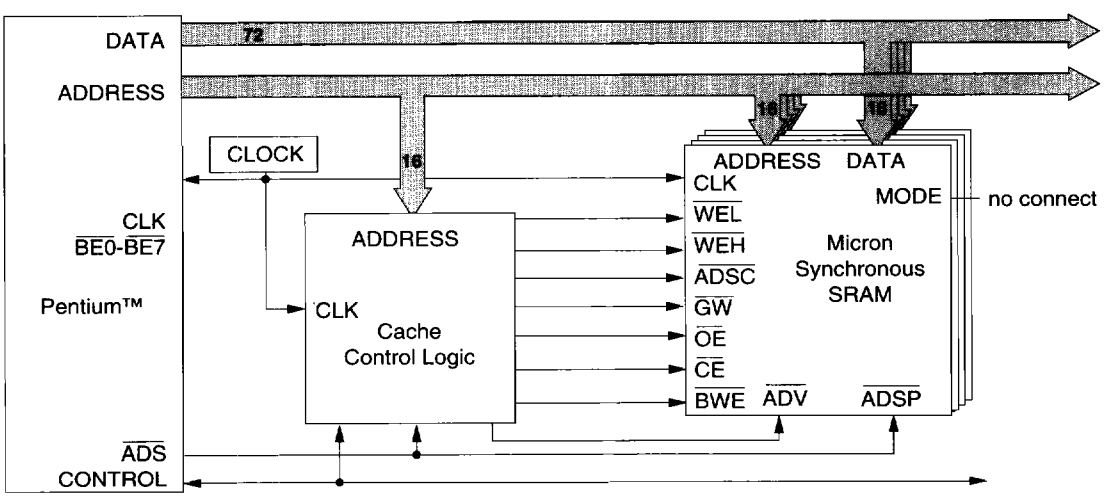


Figure 5
256K BYTE SECONDARY CACHE WITH PARITY, INTERLEAVED BURST AND DIRECT CONNECTION OF BE# LINES TO SYNCBURST SRAM

SYNCHRONOUS SRAM